



**4N60-R**

Preliminary

*Power MOSFET*

**4A, 600V N-CHANNEL  
POWER MOSFET**

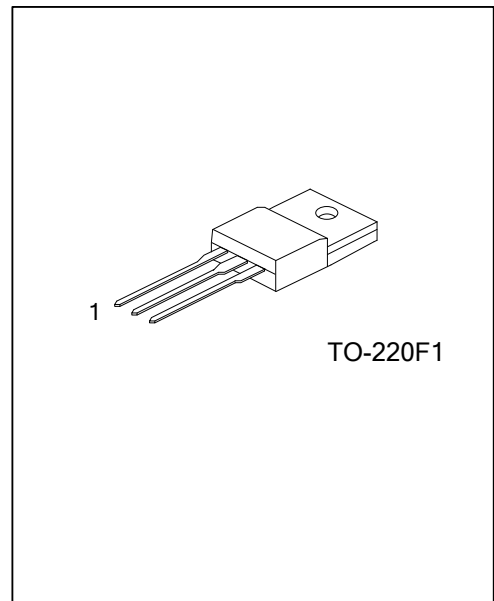
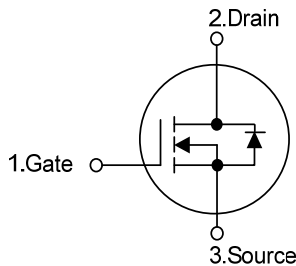
■ DESCRIPTION

The UTC **4N60-R** is a high voltage power MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

■ FEATURES

- \*  $R_{DS(ON)} < 2.5\Omega @ V_{GS} = 10V$
- \* Fast Switching Capability
- \* Avalanche Energy Specified
- \* Improved dv/dt Capability, high Ruggedness

■ SYMBOL



■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
4N60L-TF1-T	4N60G-TF1-T	TO-220F1	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>4N60L-TF1-T</p>	<p>(1) T: Tube (2) TF1: TO-220F1 (3) L: Lead Free, G: Halogen Free</p>
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■ MARKING INFORMATION

PACKAGE	MARKING
TO-220F1	

■ ABSOLUTE MAXIMUM RATINGS ( $T_C = 25^\circ\text{C}$ , unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	$V_{DSS}$	600	V
Gate-Source Voltage	$V_{GSS}$	$\pm 30$	V
Avalanche Current (Note 2)	$I_{AR}$	4	A
Drain Current	Continuous	$I_D$	4.0
	Pulsed (Note 2)	$I_{DM}$	16
Avalanche Energy	Single Pulsed (Note 3)	$E_{AS}$	160
Peak Diode Recovery dv/dt (Note 4)	dv/dt	4.5	V/ns
Power Dissipation	$P_D$	36	W
Junction Temperature	$T_J$	+150	$^\circ\text{C}$
Operating Temperature	$T_{OPR}$	-55 ~ +150	$^\circ\text{C}$
Storage Temperature	$T_{STG}$	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by maximum junction temperature

3.  $L = 20\text{mH}$ ,  $I_{AS} = 4\text{A}$ ,  $V_{DD} = 50\text{V}$ ,  $R_G = 25\ \Omega$ , Starting  $T_J = 25^\circ\text{C}$

4.  $I_{SD} \leq 4.4\text{A}$ ,  $di/dt \leq 200\text{A}/\mu\text{s}$ ,  $V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$

■ THERMAL DATA

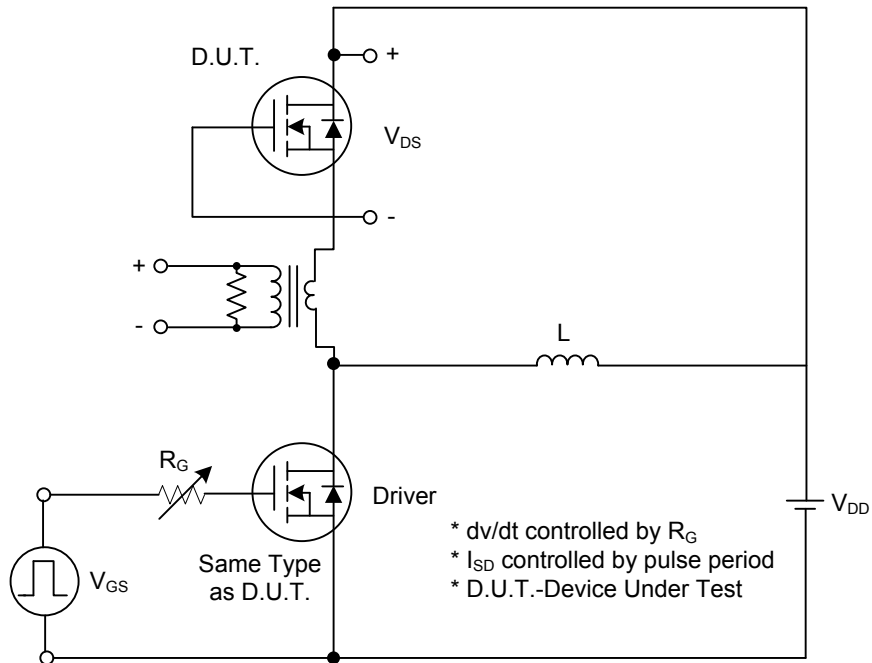
PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	$\theta_{JA}$	62.5	$^\circ\text{C}/\text{W}$
Junction to Case	$\theta_{JC}$	3.47	$^\circ\text{C}/\text{W}$

■ ELECTRICAL CHARACTERISTICS ( $T_C=25^\circ\text{C}$ , unless otherwise specified)

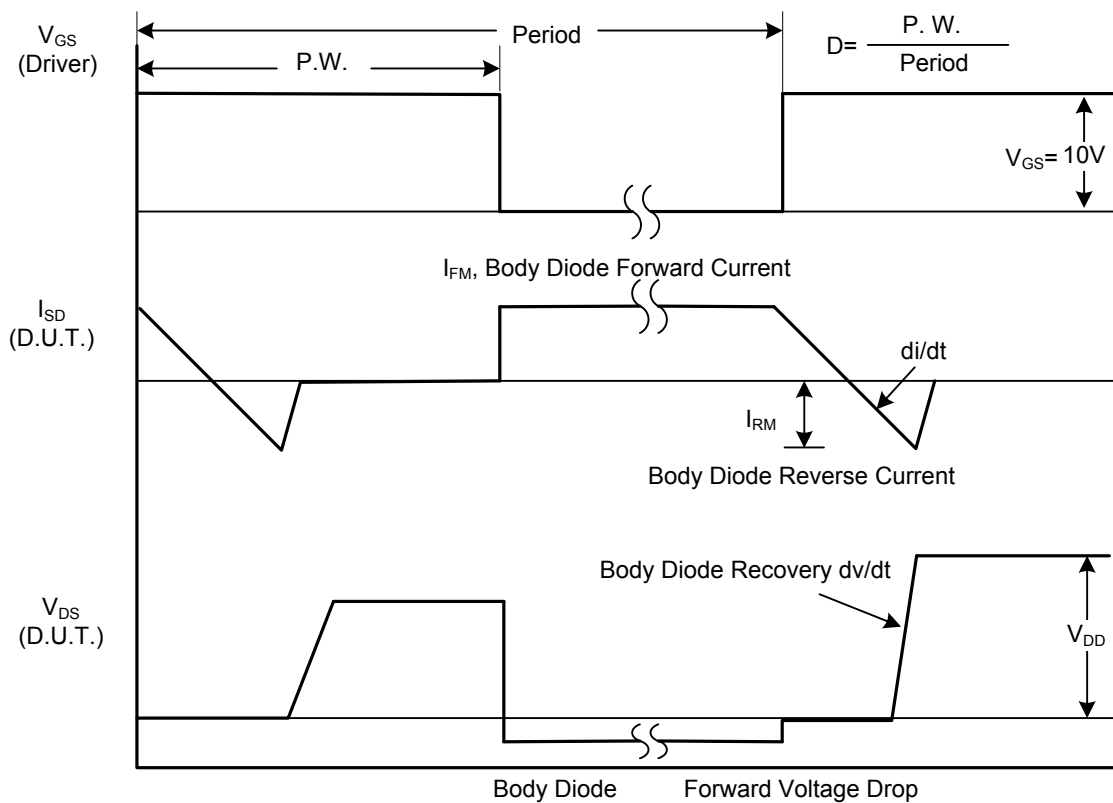
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	600			V
Drain-Source Leakage Current	$I_{DSS}$	$V_{DS}=600V, V_{GS}=0V$			10	$\mu A$
		$V_{DS}=480V, T_C=125^\circ C$			100	$\mu A$
Gate-Source Leakage Current	Forward	$I_{GSS}$				nA
	Reverse					
		$V_{GS}=-30V, V_{DS}=0V$			-100	nA
Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	$I_D=250\mu A$ , Referenced to $25^\circ C$		0.6		$V/^\circ C$
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	3.0		5.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=2.2A$		2.3	2.5	$\Omega$
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	$C_{ISS}$	$V_{DS}=25V, V_{GS}=0V, f=1MHz$		440	670	pF
Output Capacitance	$C_{OSS}$			50	100	pF
Reverse Transfer Capacitance	$C_{RSS}$			6.8	20	pF
<b>SWITCHING CHARACTERISTICS</b>						
Turn-On Delay Time	$t_{D(ON)}$	$V_{DD}=30V, I_D=0.5A, R_G=25\Omega$ (Note 1, 2)		45	60	ns
Turn-On Rise Time	$t_R$			35	55	ns
Turn-Off Delay Time	$t_{D(OFF)}$			65	85	ns
Turn-Off Fall Time	$t_F$			40	60	ns
Total Gate Charge	$Q_G$	$V_{DS}=50V, I_D=1.3A, I_D=100\mu A$ $V_{GS}=10V$ (Note 1, 2)		15	30	nC
Gate-Source Charge	$Q_{GS}$			5		nC
Gate-Drain Charge	$Q_{GD}$			15		nC
<b>SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS</b>						
Drain-Source Diode Forward Voltage	$V_{SD}$	$V_{GS}=0V, I_S=4.4A$			1.4	V
Maximum Continuous Drain-Source Diode Forward Current	$I_S$				4.4	A
Maximum Pulsed Drain-Source Diode Forward Current	$I_{SM}$				17.6	A
Reverse Recovery Time	$t_{rr}$	$V_{GS}=0V, I_S=4.4A,$		250		ns
Reverse Recovery Charge	$Q_{RR}$	$di_f/dt=100A/\mu s$ (Note 1)		1.5		$\mu C$

- Notes: 1. Pulse Test: Pulse width  $\leq 300\mu s$ , Duty cycle  $\leq 2\%$   
2. Essentially independent of operating temperature

■ TEST CIRCUITS AND WAVEFORMS

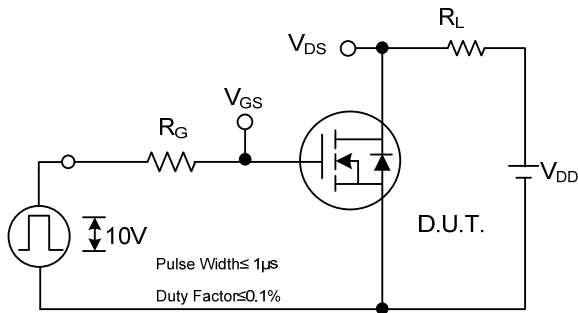


Peak Diode Recovery  $dv/dt$  Test Circuit

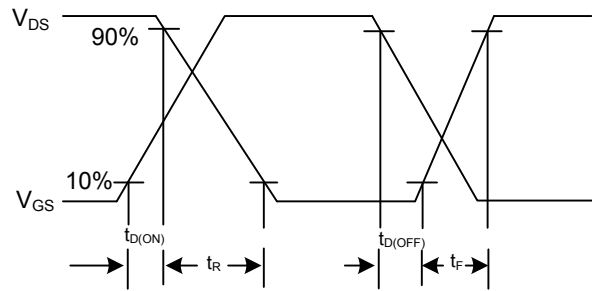


Peak Diode Recovery  $dv/dt$  Waveforms

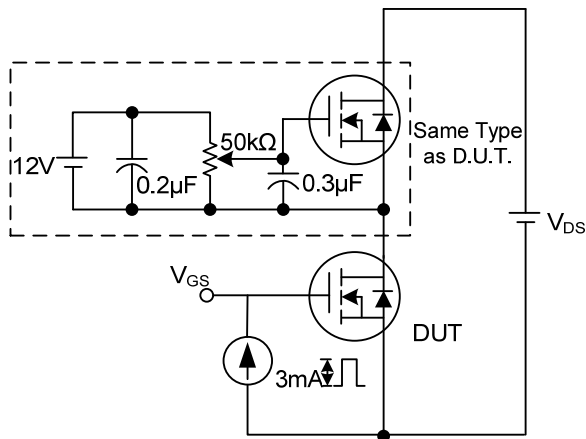
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



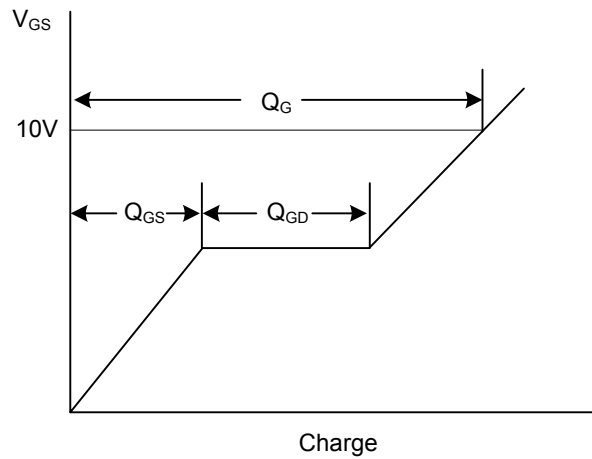
Switching Test Circuit



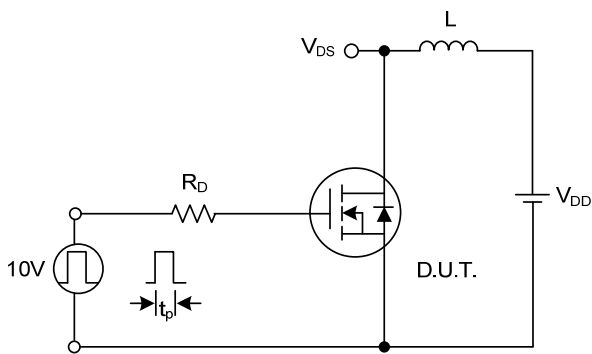
Switching Waveforms



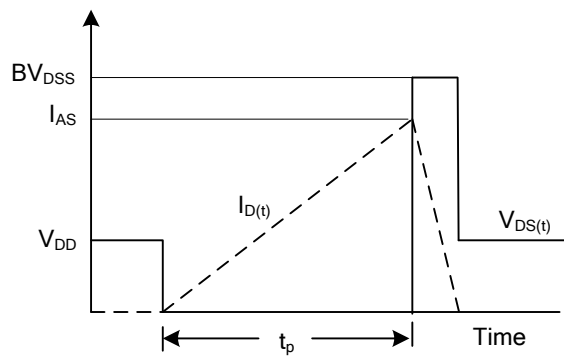
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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